



**THE DATASHEET OF
MC74HC573ADWG**



MC74HC573A

Octal 3-State Noninverting Transparent Latch

High-Performance Silicon-Gate CMOS

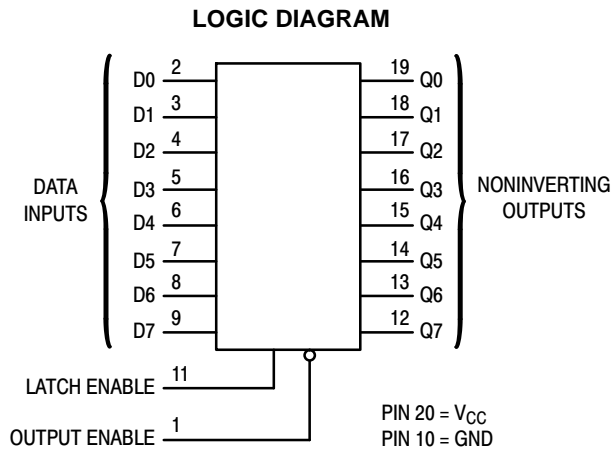
The MC74HC573A is identical in pinout to the LS573. The devices are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

These latches appear transparent to data (i.e., the outputs change asynchronously) when Latch Enable is high. When Latch Enable goes low, data meeting the setup and hold time becomes latched.

The HC573A is identical in function to the HC373A but has the data inputs on the opposite side of the package from the outputs to facilitate PC board layout.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μ A
- In Compliance with the JEDEC Standard No. 7.0 A Requirements
- Chip Complexity: 218 FETs or 54.5 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant



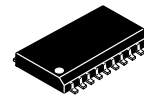
Design Criteria	Value	Units
Internal Gate Count*	54.5	ea.
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μ W
Speed Power Product	0.0075	pJ

*Equivalent to a two-input NAND gate.

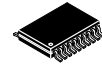


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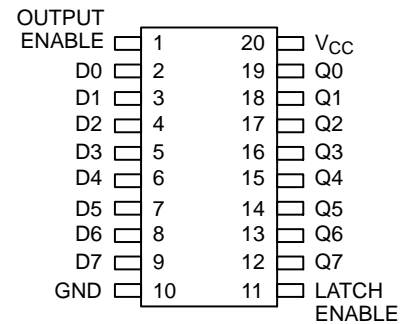


SOIC-20
DW SUFFIX
CASE 751D

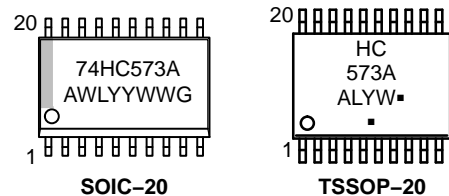


TSSOP-20
DT SUFFIX
CASE 948E

PIN ASSIGNMENT



MARKING DIAGRAMS



SOIC-20 **TSSOP-20**

A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or ■ = Pb-Free Package
(Note: Microdot may be in either location)

FUNCTION TABLE

		Inputs		Output
Output Enable	Latch Enable	D	Q	
L	H	H	H	H
L	H	L	L	L
L	L	X	X	No Change
H	X	X	X	Z

X = Don't Care
Z = High Impedance

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MC74HC573A

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
V_{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
I_{in}	DC Input Current, per Pin	± 20	mA
I_{out}	DC Output Current, per Pin	± 35	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 75	mA
P_D	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (TSSOP or SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: -7 mW/°C from 65° to 125°C
TSSOP Package: -6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	-55	+125	°C
t_r, t_f	Input Rise and Fall Time (Figure 1)	$V_{CC} = 2.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 1000 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit																																								
				-55 to 25°C	≤ 85°C	≤ 125°C																																									
V_{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \leq 20 \mu\text{A}$	2.0	1.5	1.5	1.5	V																																								
			3.0	2.1	2.1	2.1																																									
			4.5	3.15	3.15	3.15																																									
			6.0	4.2	4.2	4.2																																									
V_{IL}	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \leq 20 \mu\text{A}$	2.0	0.5	0.5	0.5	V																																								
			3.0	0.9	0.9	0.9																																									
			4.5	1.35	1.35	1.35																																									
			6.0	1.8	1.8	1.8																																									
V_{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \leq 20 \mu\text{A}$	2.0	1.9	1.9	1.9	V																																								
			4.5	4.4	4.4	4.4																																									
			6.0	5.9	5.9	5.9																																									
			$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \leq 2.4 \text{ mA}$ $ I_{out} \leq 6.0 \text{ mA}$ $ I_{out} \leq 7.8 \text{ mA}$	3.0	2.48	2.34		2.2																																							
V_{OL}	Maximum Low-Level Output Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \leq 20 \mu\text{A}$	2.0	0.1	0.1	0.1	V																																								
			4.5	0.1	0.1	0.1																																									
			6.0	0.1	0.1	0.1																																									
			$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \leq 2.4 \text{ mA}$ $ I_{out} \leq 6.0 \text{ mA}$ $ I_{out} \leq 7.8 \text{ mA}$	3.0	0.26	0.33		0.4																																							
I_{in}	Maximum Input Leakage Current	$V_{in} = V_{CC} \text{ or } GND$	6.0	± 0.1	± 1.0	± 1.0	μA																																								
			6.0	± 0.5	± 5.0	± 10																																									
								6.0	4.0	40	160	I_{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or } GND$	6.0	± 0.5	± 5.0	± 10	μA	6.0	± 0.5	± 5.0	± 10	I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC} \text{ or } GND$ $ I_{out} = 0 \mu\text{A}$	6.0	4.0	40	160	μA	6.0	4.0	40	160												
															6.0	4.0	40	160									I_{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or } GND$	6.0						± 0.5	± 5.0	± 10	μA	6.0	± 0.5	± 5.0	± 10	I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC} \text{ or } GND$ $ I_{out} = 0 \mu\text{A}$	6.0
6.0	4.0	40	160																																												
				I_{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or } GND$	6.0	± 0.5	± 5.0	± 10	μA									6.0	± 0.5	± 5.0	± 10							I_{CC}		Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC} \text{ or } GND$ $ I_{out} = 0 \mu\text{A}$	6.0	4.0	40	160	μA									6.0
							I_{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or } GND$	6.0		± 0.5	± 5.0	± 10	μA	6.0	± 0.5	± 5.0	± 10					I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC} \text{ or } GND$ $ I_{out} = 0 \mu\text{A}$					6.0			4.0	40	160	μA			6.0	4.0	40	160				
I_{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or } GND$	6.0							± 0.5		± 5.0	± 10	μA																																	
			6.0							± 0.5		± 5.0	± 10																																		
				I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC} \text{ or } GND$ $ I_{out} = 0 \mu\text{A}$					6.0					4.0	40	160	μA	6.0	4.0	40	160																								
							I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC} \text{ or } GND$ $ I_{out} = 0 \mu\text{A}$		6.0				4.0	40	160	μA						6.0	4.0	40	160																				
I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC} \text{ or } GND$ $ I_{out} = 0 \mu\text{A}$	6.0							4.0	40	160	μA																																		
			6.0							4.0	40	160																																			

MC74HC573A

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6.0 ns)

Symbol	Parameter	V _{CC} V	Guaranteed Limit			Unit
			-55 to 25°C	≤ 85°C	≤ 125°C	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input D to Q (Figures 1 and 5)	2.0	150	190	225	ns
		3.0	100	140	180	
		4.5	30	38	45	
		6.0	26	33	38	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Latch Enable to Q (Figures 2 and 5)	2.0	160	200	240	ns
		3.0	105	145	190	
		4.5	32	40	48	
		6.0	27	34	41	
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)	2.0	150	190	225	ns
		3.0	100	125	150	
		4.5	30	38	45	
		6.0	26	33	38	
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)	2.0	150	190	225	ns
		3.0	100	125	150	
		4.5	30	38	45	
		6.0	26	33	38	
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 5)	2.0	60	75	90	ns
		3.0	27	32	36	
		4.5	12	15	18	
		6.0	10	13	15	
C _{in}	Maximum Input Capacitance		10	10	10	pF
C _{out}	Maximum 3-State Output Capacitance (Output in High-Impedance State)		15	15	15	pF
C _{PD}	Power Dissipation Capacitance (Per Enabled Output)*	Typical @ 25°C, V _{CC} = 5.0 V			pF	
		23				

* Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

TIMING REQUIREMENTS (C_L = 50 pF, Input t_r = t_f = 6.0 ns)

Symbol	Parameter	Figure	V _{CC} V	Guaranteed Limit						Unit
				-55 to 25°C		≤ 85°C		≤ 125°C		
				Min	Max	Min	Max	Min	Max	
t _{su}	Minimum Setup Time, Input D to Latch Enable	4	2.0	50		65		75		ns
			3.0	40		50		60		
			4.5	10		13		15		
			6.0	9.0		11		13		
t _h	Minimum Hold Time, Latch Enable to Input D	4	2.0	5.0		5.0		5.0		ns
			3.0	5.0		5.0		5.0		
			4.5	5.0		5.0		5.0		
			6.0	5.0		5.0		5.0		
t _w	Minimum Pulse Width, Latch Enable	2	2.0	75		95		110		ns
			3.0	60		80		90		
			4.5	15		19		22		
			6.0	13		16		19		
t _r , t _f	Maximum Input Rise and Fall Times	1	2.0		1000		1000		1000	ns
			3.0		800		800		800	
			4.5		500		500		500	
			6.0		400		400		400	

MC74HC573A

SWITCHING WAVEFORMS

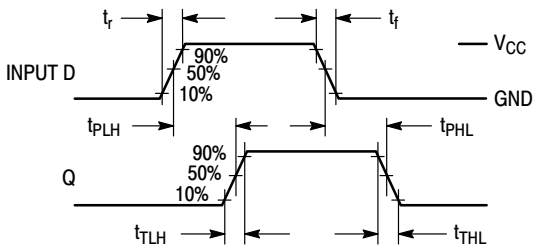


Figure 1.

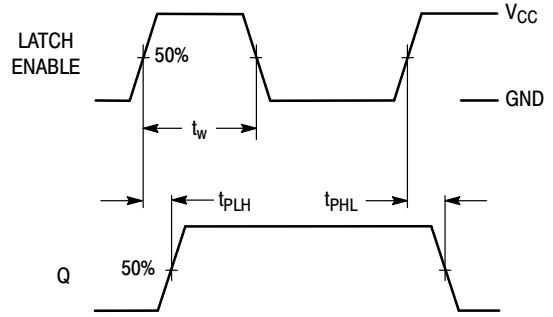


Figure 2.

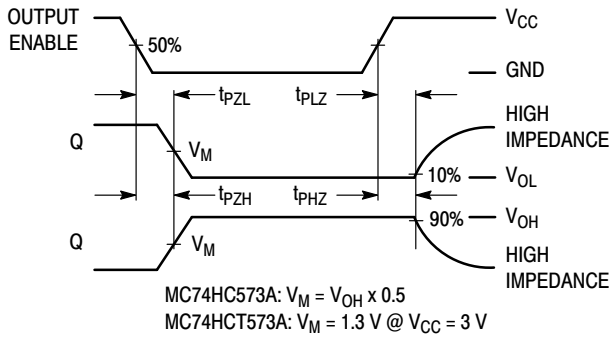


Figure 3.

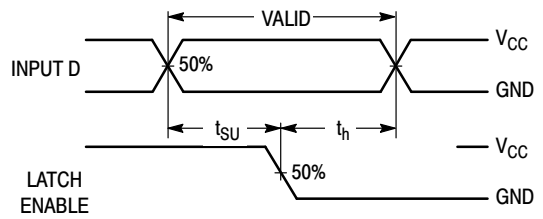
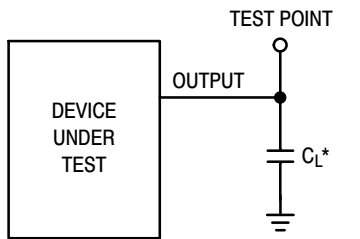
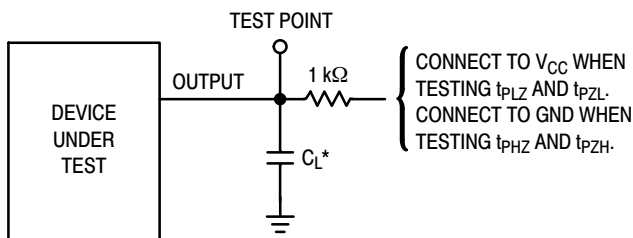


Figure 4.



*Includes all probe and jig capacitance

Figure 5. Test Circuit



*Includes all probe and jig capacitance

Figure 6. Test Circuit

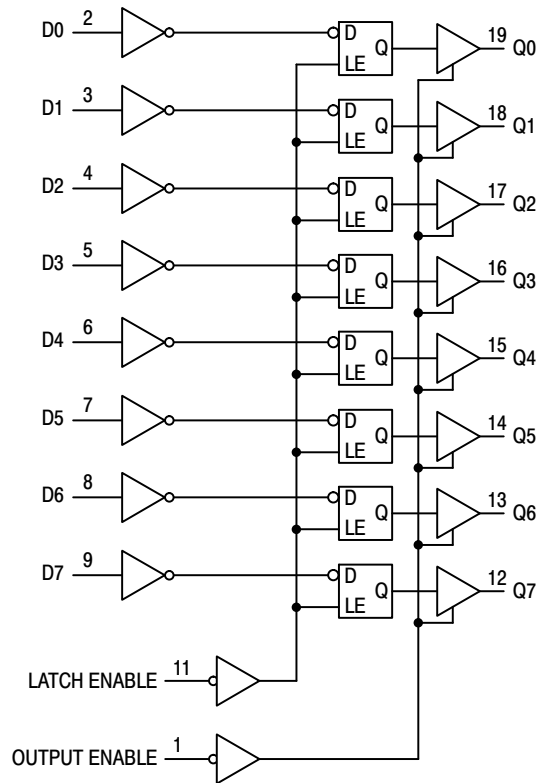


Figure 7. EXPANDED LOGIC DIAGRAM

MC74HC573A

ORDERING INFORMATION

Device	Package	Shipping†
MC74HC573ADWG	SOIC-20 WIDE (Pb-Free)	38 Units / Rail
MC74HC573ADWR2G	SOIC-20 WIDE (Pb-Free)	1000 Tape & Reel
MC74HC573ADTG	TSSOP-20 (Pb-Free)	75 Units / Rail
MC74HC573ADTR2G	TSSOP-20 (Pb-Free)	2500 Tape & Reel
NLV74HC573ADTR2G*	TSSOP-20 (Pb-Free)	2500 Tape & Reel

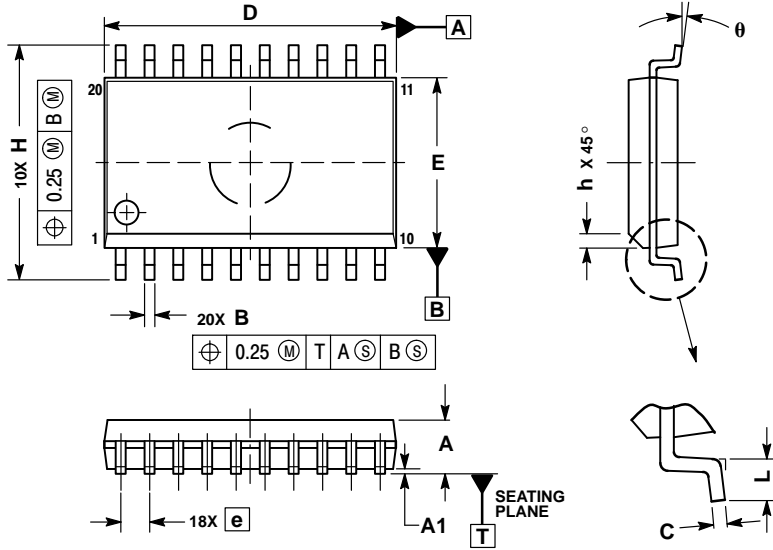
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

MC74HC573A

PACKAGE DIMENSIONS

SOIC-20
DW SUFFIX
CASE 751D-05
ISSUE H

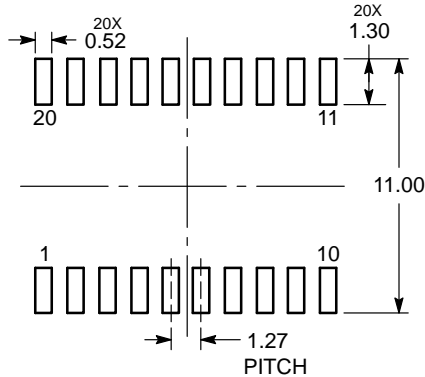


NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS	
	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
B	0.35	0.49
C	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0°	7°

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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